TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET TIM5867-30UL

FEATURES

■ HIGH POWER

■ HIGH GAIN

- BROAD BAND INTERNALLY MATCHED FET
- P1dB=45.0 dBm at 5.85GHz to 6.75GHz
- HERMETICALLY SEALED PACKAGE
- G1dB=10.0dB at 5.85GHz to 6.75GHz

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain	P1dB		dBm	44.0	45.0	_
Compression Point						
Power Gain at 1dB Gain	G1dB	VDS= 10V	dB	9.0	10.0	_
Compression Point		IDSset=6.4A				
Drain Current	IDS1	f = 5.85 to 6.75GHz	Α	_	7.0	8.0
Gain Flatness	ΔG		dB	_		±0.8
Power Added Efficiency	ηadd		%		41	
3rd Order Intermodulation	IM3	Two-Tone Test	dBc	-44	-47	_
Distortion		Po=34.0 dBm				
Drain Current	IDS2	(Single Carrier Level)	Α		7.0	8.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C		_	100

Recommended gate resistance(Rg) : Rg= 28 Ω (MAX.)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V	S		8.0	
		IDS= 10.0A				
Pinch-off Voltage	VGSoff	VDS= 3V	V	-0.5	-2.0	-3.0
		IDS= 80mA				
Saturated Drain Current	IDSS	VDS= 3V	Α		16.0	
		VGS= 0V				
Gate-Source Breakdown	VGSO	IGS=-240μA	V	-5	_	_
Voltage						
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.0	1.5

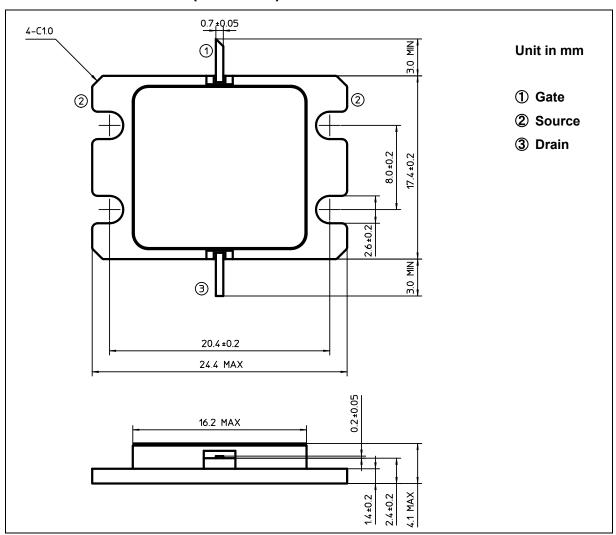
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	18.0
Total Power Dissipation (Tc= 25 °C)	PT	W	100
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA05A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.